

# 1.5V Drive Pch MOSFET

## RQ1A070AP

### ● Structure

Silicon P-channel MOSFET

### ● Features

- 1) Low on-resistance.
- 2) Low voltage drive (1.5V drive).
- 3) Small surface mount package (TSMT8).

### ● Application

Switching

### ● Packaging specifications

| Type      | Package                      | Taping |
|-----------|------------------------------|--------|
|           | Code                         | TR     |
|           | Basic ordering unit (pieces) | 3000   |
| RQ1A070AP |                              | ○      |

### ● Absolute maximum ratings (Ta = 25°C)

| Parameter                    | Symbol     | Limits      | Unit       |
|------------------------------|------------|-------------|------------|
| Drain-source voltage         | $V_{DSS}$  | -12         | V          |
| Gate-source voltage          | $V_{GSS}$  | 0 to -8     | V          |
| Drain current                | Continuous | $I_D$       | $\pm 7$ A  |
|                              | Pulsed     | $I_{DP}$ *1 | $\pm 28$ A |
| Source current (Body Diode)  | Continuous | $I_S$       | -1 A       |
|                              | Pulsed     | $I_{SP}$ *1 | -28 A      |
| Power dissipation            | $P_D$ *2   | 1.5         | W          |
| Channel temperature          | $T_{ch}$   | 150         | °C         |
| Range of storage temperature | $T_{stg}$  | -55 to +150 | °C         |

\*1  $P_w \leq 10 \mu s$ , Duty cycle  $\leq 1\%$

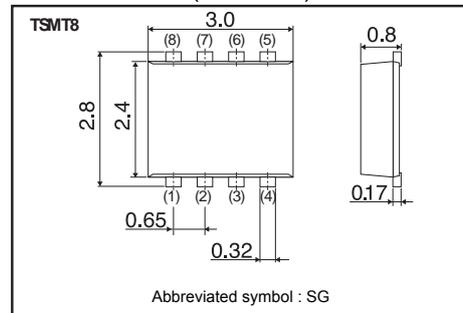
\*2 Mounted on a ceramic board.

### ● Thermal resistance

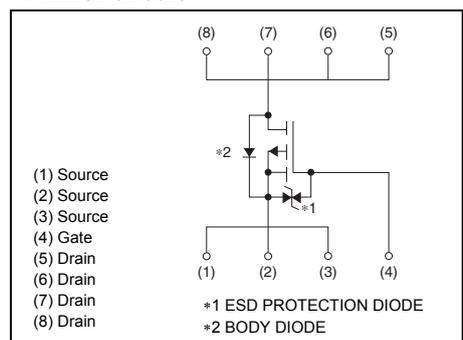
| Parameter          | Symbol           | Limits | Unit   |
|--------------------|------------------|--------|--------|
| Channel to Ambient | $R_{th}(ch-a)^*$ | 83.3   | °C / W |

\*Mounted on a ceramic board.

### ● Dimensions (Unit : mm)



### ● Inner circuit



**● Electrical characteristics (Ta = 25°C)**

| Parameter                               | Symbol         | Min. | Typ. | Max. | Unit       | Conditions                    |
|---|----------------|------|------|------|------------|-------------------------------|
| Gate-source leakage                     | $I_{GSS}$      | -    | -    | -10  | $\mu A$    | $V_{GS} = -8V, V_{DS} = 0V$   |
| Drain-source breakdown voltage          | $V_{(BR)DSS}$  | -12  | -    | -    | V          | $I_D = -1mA, V_{GS} = 0V$     |
| Zero gate voltage drain current         | $I_{DSS}$      | -    | -    | -10  | $\mu A$    | $V_{DS} = -12V, V_{GS} = 0V$  |
| Gate threshold voltage                  | $V_{GS(th)}$   | -0.3 | -    | -1.0 | V          | $V_{DS} = -6V, I_D = -1mA$    |
| Static drain-source on-state resistance | $R_{DS(on)}$ * | -    | 10   | 14   | m $\Omega$ | $I_D = -7A, V_{GS} = -4.5V$   |
|   |                | -    | 13   | 19   |            | $I_D = -3.5A, V_{GS} = -2.5V$ |
|   |                | -    | 18   | 27   |            | $I_D = -3.5A, V_{GS} = -1.8V$ |
|   |                | -    | 24   | 48   |            | $I_D = -1.4A, V_{GS} = -1.5V$ |
| Forward transfer admittance             | $ Y_{fs} $ *   | 11   | -    | -    | S          | $V_{DS} = -6V, I_D = -7A$     |
| Input capacitance                       | $C_{iss}$      | -    | 7800 | -    | pF         | $V_{DS} = -6V$                |
| Output capacitance                      | $C_{oss}$      | -    | 900  | -    | pF         | $V_{GS} = 0V$                 |
| Reverse transfer capacitance            | $C_{rss}$      | -    | 850  | -    | pF         | $f = 1MHz$                    |
| Turn-on delay time                      | $t_{d(on)}$ *  | -    | 25   | -    | ns         | $V_{DD} = -6V, I_D = -3.5A,$  |
| Rise time                               | $t_r$ *        | -    | 135  | -    | ns         | $V_{GS} = -4.5V$              |
| Turn-off delay time                     | $t_{d(off)}$ * | -    | 550  | -    | ns         | $R_L = 1.7\Omega$             |
| Fall time                               | $t_f$ *        | -    | 260  | -    | ns         | $R_G = 10\Omega$              |
| Total gate charge                       | $Q_g$ *        | -    | 80   | -    | nC         | $V_{DD} = -6V, I_D = -7A,$    |
| Gate-source charge                      | $Q_{gs}$ *     | -    | 12   | -    | nC         | $V_{GS} = -4.5V$              |
| Gate-drain charge                       | $Q_{gd}$ *     | -    | 13   | -    | nC         |                               |

\*Pulsed

**● Body diode characteristics (Source-Drain)**

| Parameter       | Symbol     | Min. | Typ. | Max. | Unit | Conditions               |
|-----------------|------------|------|------|------|------|--------------------------|
| Forward Voltage | $V_{SD}$ * | -    | -    | -1.2 | V    | $I_S = -7A, V_{GS} = 0V$ |

\*Pulsed

●Electrical characteristic curves (Ta=25°C)

Fig.1 Typical Output Characteristics ( I )

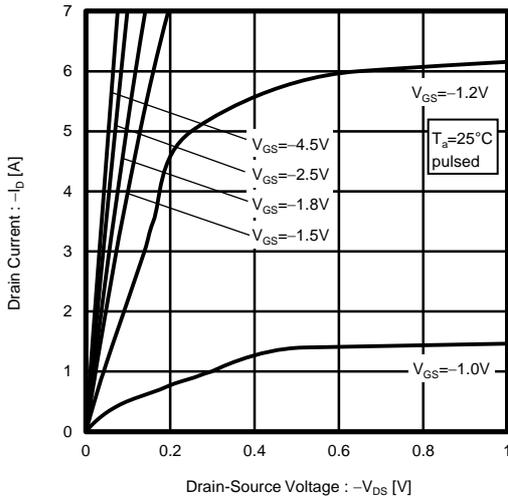


Fig.2 Typical Output Characteristics ( II )

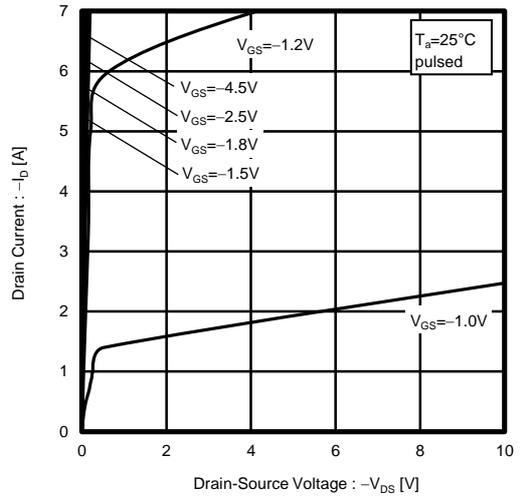


Fig.3 Static Drain-Source On-State Resistance vs. Drain Current

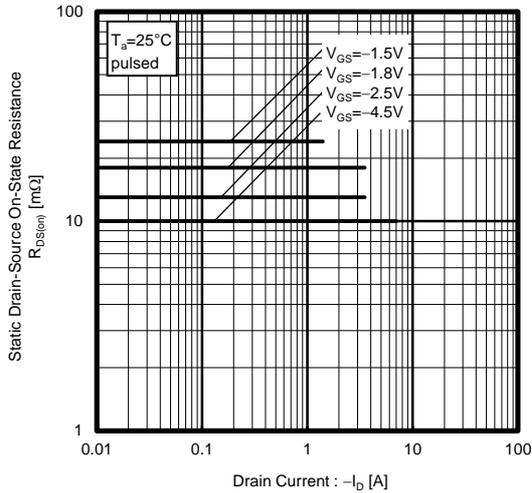


Fig.4 Static Drain-Source On-State Resistance vs. Drain Current

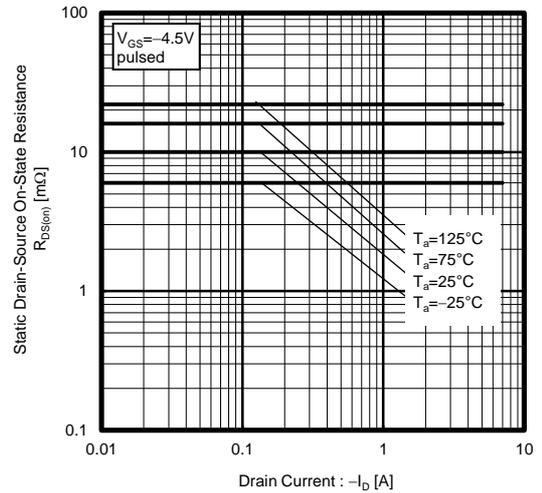


Fig.5 Static Drain-Source On-State Resistance vs. Drain Current

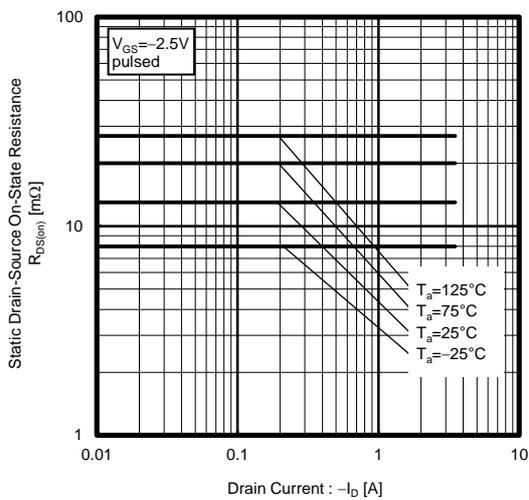


Fig.6 Static Drain-Source On-State Resistance vs. Drain Current

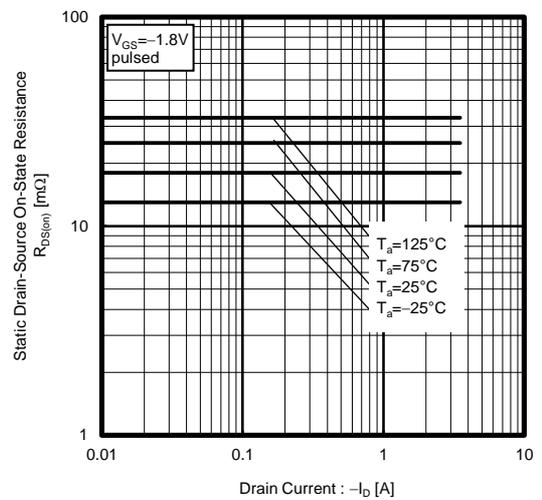


Fig.7 Static Drain-Source On-State Resistance vs. Drain Current

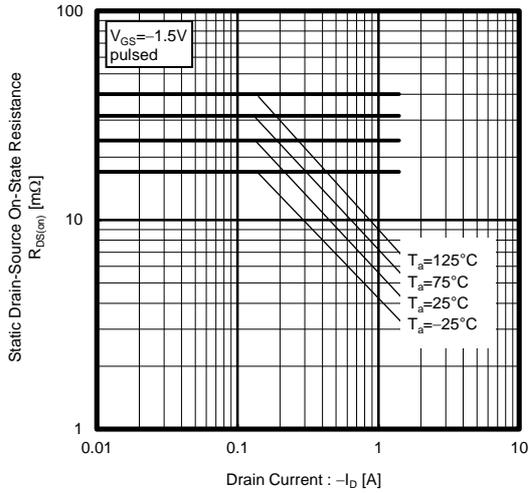


Fig.8 Forward Transfer Admittance vs. Drain Current

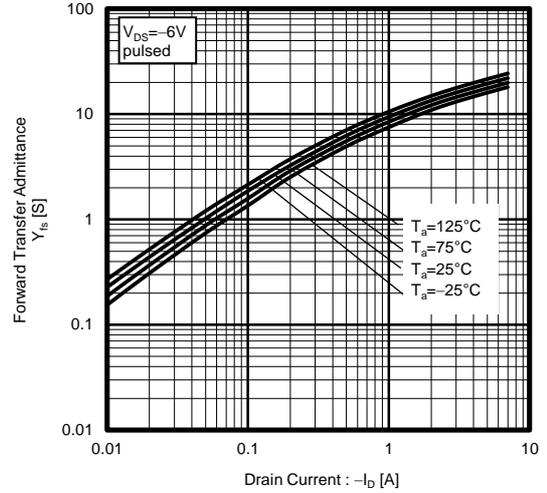


Fig.9 Typical Transfer Characteristics

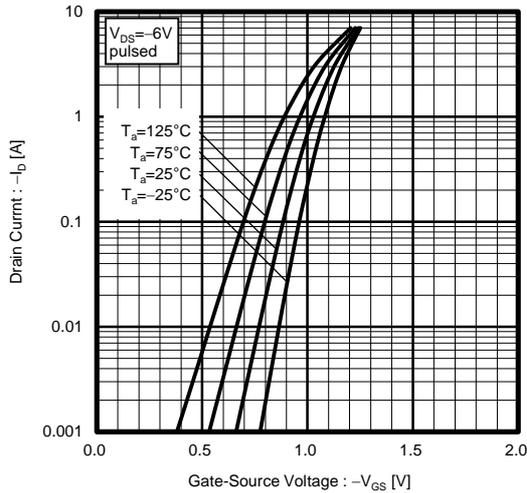


Fig.10 Source Current vs. Source-Drain Voltage

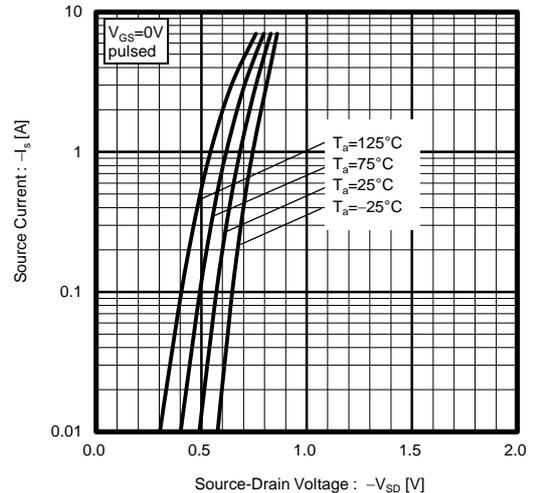


Fig.11 Static Drain-Source On-State Resistance vs. Gate-Source Voltage

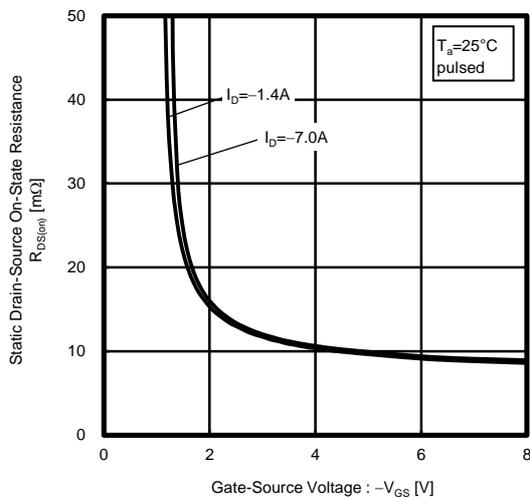


Fig.12 Switching Characteristics

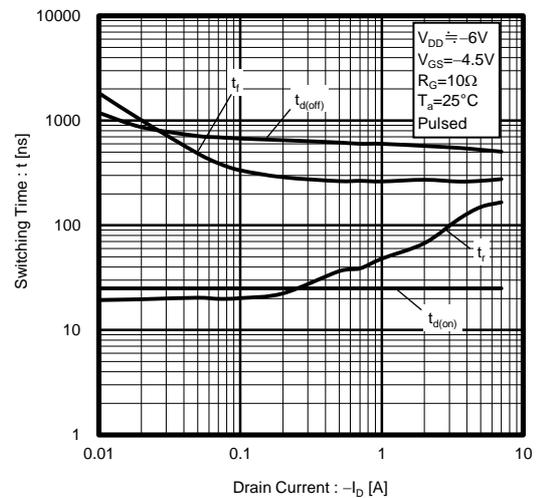


Fig.13 Dynamic Input Characteristics

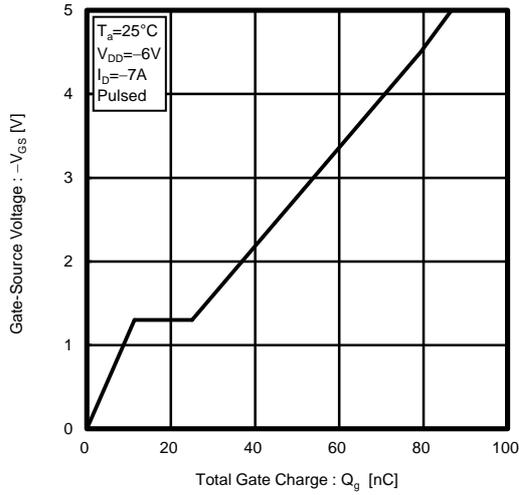


Fig.14 Typical Capacitance vs. Drain-Source Voltage

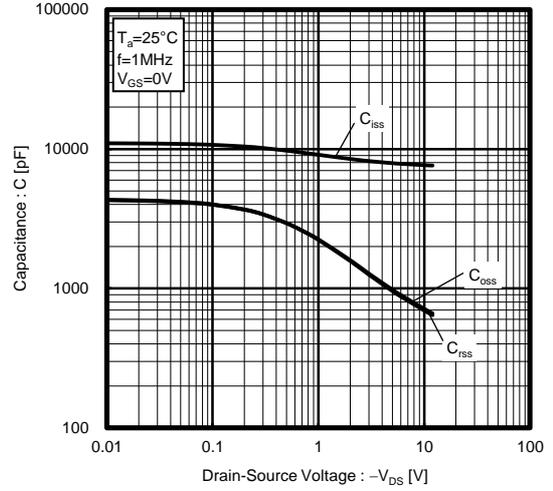


Fig.15 Maximum Safe Operating Area

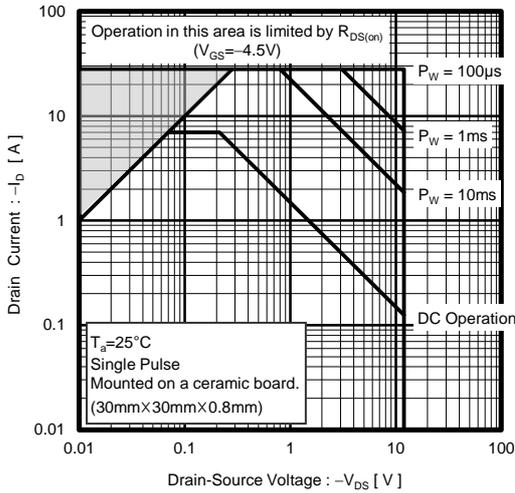
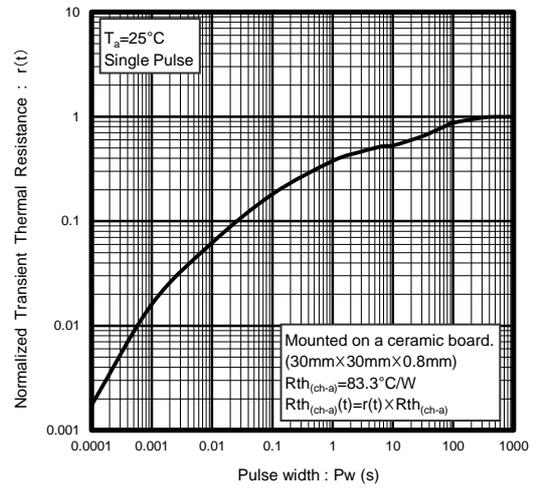


Fig.16 Normalized Transient Thermal Resistance v.s. Pulse Width



● Measurement circuits

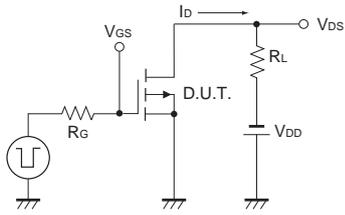


Fig.1-1 Switching Time Measurement Circuit

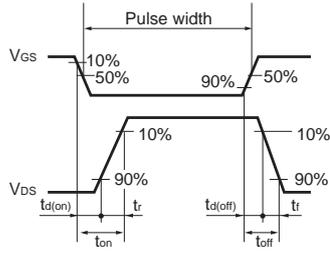


Fig.1-2 Switching Waveforms

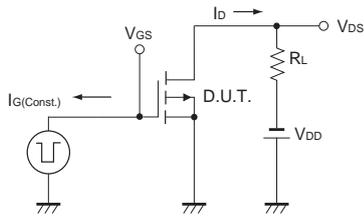


Fig.2-1 Gate Charge Measurement Circuit

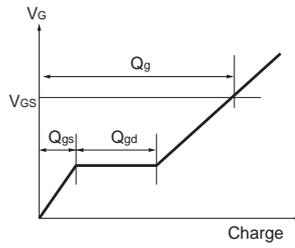


Fig.2-2 Gate Charge Waveform

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